

Vishay Semiconductors

Phase Control Thyristors (Stud Version), 110 A



PRODUCT SUMMARY				
I _{T(AV)}	110 A			
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V			
V _{TM}	1.57 V			
I _{GT}	80 mA			
TJ	-40 °C to 140 °C			
Package	TO-209AC (TO-94)			
Diode variation	Single SCR			

FEATURES

- High current and high surge ratings
- Hermetic ceramic housing
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		110	A			
I _{T(AV)}	T _C	90	°C			
I _{T(RMS)}		172				
1	50 Hz	2080	A			
ITSM	60 Hz	2180				
l ² t	50 Hz	21.7	kA ² s			
1-1	60 Hz	19.8	KA-S			
V _{DRM} /V _{RRM}		400 to 1200	V			
t _q	Typical	110	μs			
TJ		-40 to 140	°C			

ELECTRICAL SPECIFICATIONS

VOLTAG	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{DRM} /I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA					
	40	400	500						
VS-110RKI VS-111RKI	80	800	900	20					
	120	1200	1300						

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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I	180° condu	ction, half sine v	NOVO	110	А
at case temperature	I _{T(AV)}	160 Condu	cuon, nan sine i	wave	90	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 83 °C	case temperat	ure	172	
		t = 10 ms	No voltage		2080	
Maximum peak, one-cycle	1	t = 8.3 ms	reapplied		2180	А
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave,	1750	
		t = 8.3 ms	reapplied		1830	
Marian and Participation	t = 10 ms t = 8.3 ms	No voltage	initial $T_J = T_J$ maximum	21.7		
		t = 8.3 ms	reapplied		19.8	kA ² s
Maximum I ² t for fusing	1 - 1	t = 10 ms 100 % V _{RRM}		15.3	KA-S	
		t = 8.3 ms	reapplied			14.0
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms t	o 10 ms, no volt	age reapplied	217	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.82	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			2.16	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			1.70	1112.2
Maximum on-state voltage	V _{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.57	V
Maximum holding current	Ι _Η	T 05 90	onodo oupple C	V registive land	200	A
Typical latching current	١L	$T_J = 25 \text{ °C}$, anode supply 6 V resistive load 400		400	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq$ 1 μs $T_J = T_J$ maximum, anode voltage \leq 80 % V_{DRM}	300	A/µs				
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/µs V _d = 0.67 % V _{DRM} , T _J = 25 °C	1	5				
Typical turn-off time	t _q	I_{TM} = 50 A, T _J = T _J maximum, dl/dt = - 5 A/µs V _R = 50 V, dV/dt = 20 V/µs, gate 0 V 25 Ω	110	μs				

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs				
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA				

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TRIGGERING						
PARAMETER	SYMBOL	тгет	VAL	UNITS		
PARAMETER	STIVIDUL	TEST CONDITIONS		TYP.	MAX.	
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	1	2	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0	~~~
Maximum peak positive gate current	I _{GM}			3	.0	А
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 ms$	20		v
Maximum peak negative gate voltage	- V _{GM}				0	v
		T _J = - 40 °C		180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate	80	120	mA
		T _J = 140 °C	trigger/current/voltage are the lowest value which will	40	-	
		T _J = - 40 °C	trigger all units 12 V anode	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	to cathode applied	1.6	2	V
		T _J = 140 °C		1	-	
DC gate current not to trigger	I _{GD}	T.j = T.j maximum	Maximum gate current/ voltage not to trigger is the maximum value which will	6	.0	mA
DC gate voltage not to trigger	V _{GD}	ij – ijilidAilliulli	not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		v

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 140	J°		
Maximum storage temperature range	T _{Stg}		-40 to 150	Ŀ		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.27	K/W		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1	r./ vv		
Mounting torque + 10.0/		Non-lubricated threads	15.5 (137)	N·m		
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)		
Approximate weight			130	g		
Case style	See dimensions - link at the end of datasheet TO-209AC (TO-			(TO-94)		

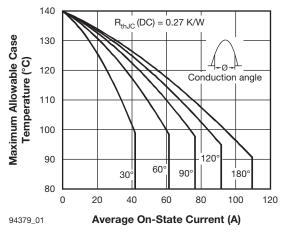
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS				
180°	0.043	0.031						
120°	0.052	0.053						
90°	0.066	0.071	$T_J = T_J maximum$	K/W				
60°	0.096	0.101]					
30°	0.167	0.169]					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

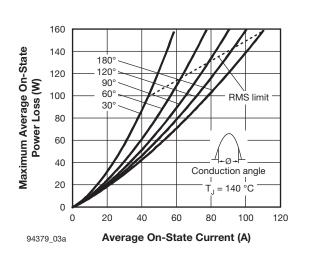
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Fig. 1 - Current Ratings Characteristics



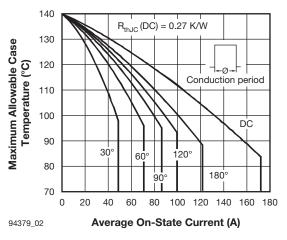


Fig. 2 - Current Ratings Characteristics

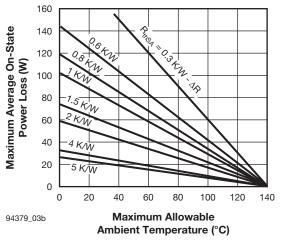
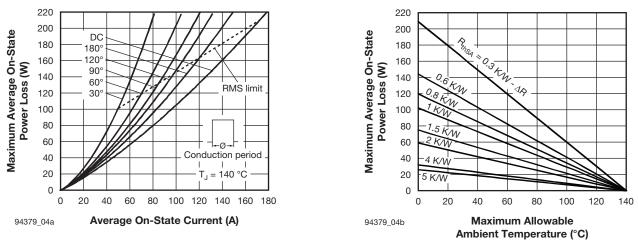
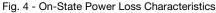


Fig. 3 - On-State Power Loss Characteristics





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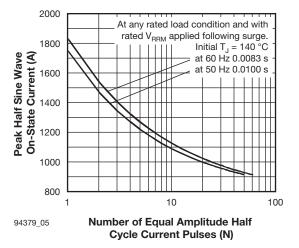
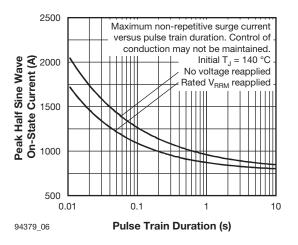


Fig. 5 - Maximum Non-Repetitive Surge Current





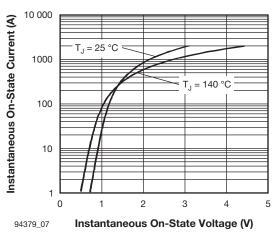
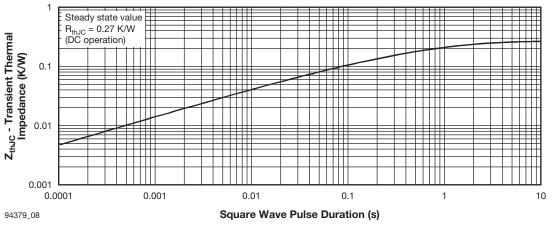


Fig. 7 - On-State Voltage Drop Characteristics





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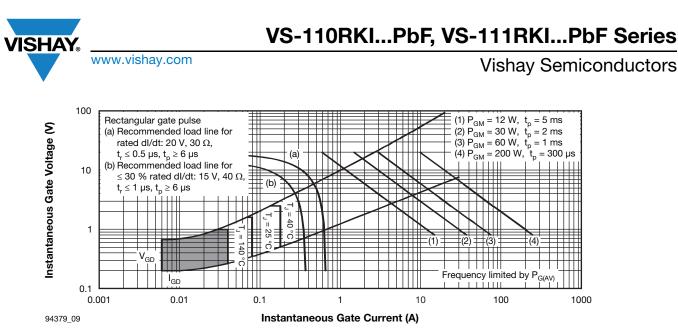


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	11	0	RKI	120	PbF
		2	3	4	5	6
	1 - 2 - 3 - 4 - 5 - 6 -	I _{T(A} ● 0 ● 1 Thy Vol ● N	V) rated = Eyele = Fast- vristor tage coo	nicondu average et termin on termi de x 10 = tandard ad (Pb)-	e output als (gate nals (ga = V _{RRM} (product	current e and a ite and (see Vo

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95003			



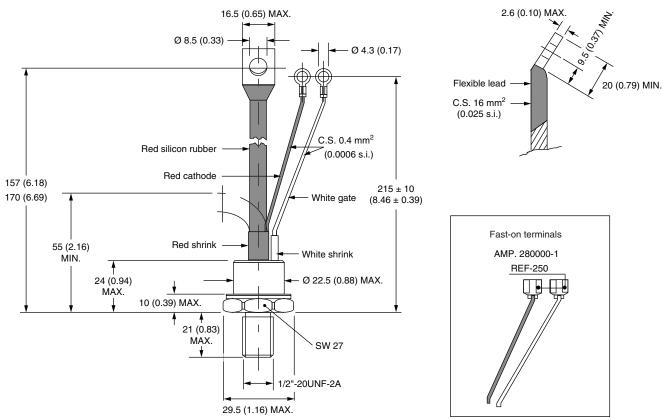
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TO-209AC (TO-94) for 110RKI and 111RKI Series

DIMENSIONS in millimeters (inches)

SHA





Note

[•] For metric device: M12 x 1.75 contact factory



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